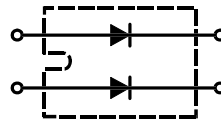


# HiPerDynFRED™ Epitaxial Diode with soft recovery

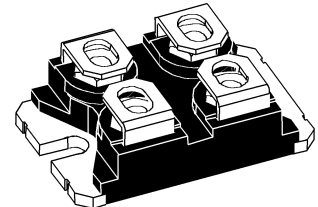
$I_{FAV} = 2x 25 A$   
 $V_{RRM} = 1200 V$   
 $t_{rr} = 20 ns$

Preliminary Data

$V_{RSM}$ V	$V_{RRM}$ V	Type
1200	1200	DSEP 2x 25-12C



miniBLOC, SOT-227 B



Symbol	Test Conditions	Maximum Ratings	
$I_{FRMS}$		35	A
$I_{FAVM}$	$T_C = 70^\circ C$ ; rectangular, $d = 0.5$	25	A
$I_{FRM}$	$t_p < 10 \mu s$ ; rep. rating, pulse width limited by $T_{VJM}$	tbd	A
$I_{FSM}$	$T_{VJ} = 45^\circ C$ ; $t_p = 10 ms$ (50 Hz), sine	250	A
$E_{AS}$	$T_{VJ} = 25^\circ C$ ; non-repetitive $I_{AS} = 1.3 A$ ; $L = 180 \mu H$	0.2	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_R$ typ.; $f = 10 kHz$ ; repetitive	0.1	A
$T_{VJ}$		-40...+150	°C
$T_{VJM}$		150	°C
$T_{stg}$		-40...+150	°C
$P_{tot}$	$T_C = 25^\circ C$	140	W
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 mA$	2500	V~
$M_d$	mounting torque (M4)	1.1-1.5/9-13	Nm/lb.in.
	terminal connection torque (M4)	1.1-1.5/9-13	Nm/lb.in.
Weight	typical	30	g

**Features**

- International standard package miniBLOC
- Isolation voltage 2500 V~
- UL registered E 72873
- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour

**Applications**

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

**Advantages**

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{RM}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Symbol	Test Conditions	Characteristic Values	
		typ.	max.
$I_R$ ①	$V_R = V_{RRM}$ ; $T_{VJ} = 25^\circ C$ $T_{VJ} = 150^\circ C$	0.25	mA
		2.0	mA
$V_F$ ②	$I_F = 25 A$ ; $T_{VJ} = 125^\circ C$ $T_{VJ} = 25^\circ C$	3.30	V
		4.80	V
$R_{thJC}$		0.9	K/W
$R_{thCH}$	with heatsink compound	0.1	K/W
$t_{rr}$	$I_F = 1 A$ ; $-di/dt = 200 A/\mu s$ ; $V_R = 30 V$ ; $T_{VJ} = 25^\circ C$	20	ns
$I_{RM}$	$V_R = 100 V$ ; $I_F = 50 A$ ; $-di_F/dt = 100 A/\mu s$ $T_{VJ} = 100^\circ C$	4.0	tbd

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %  
 ② Pulse Width = 300  $\mu s$ , Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.